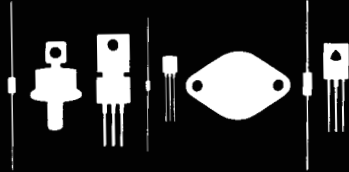


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145 Adams Avenue
Hauppauge, New York 11788



MM4000 THRU MM4003

PNP SILICON TRANSISTOR

JEDEC TO-39 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR MM4000 series types are silicon PNP transistors manufactured by the epitaxial planar process mounted in a hermetically sealed metal case designed for high current amplifier.

MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise noted)

	SYMBOL	MM4000	MM4001	MM4002	MM4003	UNIT
Collector-Base Voltage	V_{CB0}	100	150	200	250	V
Collector-Emitter Voltage	V_{CE0}	100	150	200	250	V
Emitter-Base Voltage	V_{EBO}	4.0	4.0	4.0	4.0	V
Collector Current	I_C	500	500	500	500	mA
Power Dissipation	P_D	1.0	1.0	1.0	1.0	W
Power Dissipation ($T_C=25^\circ\text{C}$)	P_D	5.0	5.0	5.0	5.0	W
Operating and Storage Junction Temperature	T_J, T_{STG}		-65 to +200			$^\circ\text{C}$
Thermal Resistance	θ_{JA}	175	175	175	175	$^\circ\text{C/W}$
Thermal Resistnace	θ_{JC}	35	35	35	35	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MM4000		MM4001		MM4002		MM4003		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
I_{CB0}	$V_{CB}=50\text{V}$		1.0		-		-		-	μA
I_{CB0}	$V_{CB}=75\text{V}$		-		1.0		-		-	μA
I_{CB0}	$V_{CB}=150\text{V}$		-		-		5.0		5.0	μA
BV_{CB0}	$I_C=100\mu\text{A}$	100		150		200		250		V
BV_{CE0}	$I_C=10\text{mA}$	100		150		200		250		V
BV_{EBO}	$I_E=100\mu\text{A}$	4.0		4.0		4.0		4.0		V
$V_{CE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$		0.6		0.6		5.0		5.0	V
h_{FE}	$V_{CE}=10\text{V}, I_C=10\text{mA}$	20		20		20		20		
C_{ob}	$V_{CB}=20\text{V}, I_E=0, f=100\text{kHz}$		6.0		-		-		-	pF
C_{ob}	$V_{CB}=20\text{V}, I_E=0, f=100\text{kHz}$		-		10		-		-	pF
C_{ob}	$V_{CB}=20\text{V}, I_E=0, f=100\text{kHz}$		-		-		20		20	pF